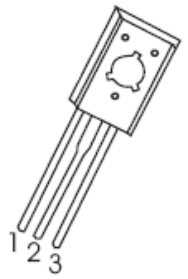
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126 Plastic-Encapsulate Transistors

D882 TRANSISTOR (NPN)

TO-126



FEATURES

- Power Dissipation

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	1.25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

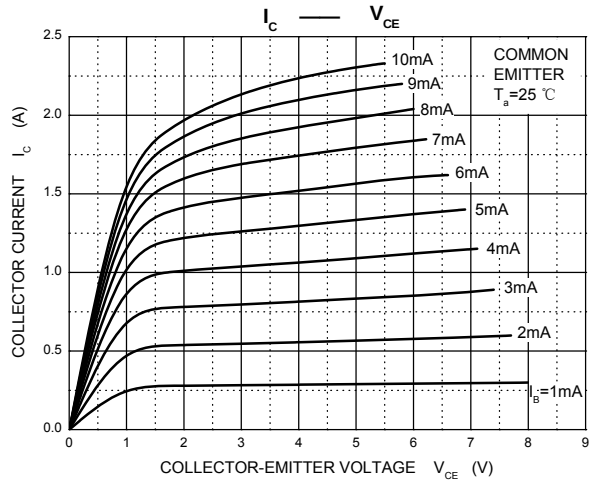
ELECTRICAL CHARACTERISTICS (T_a=25 ℃ unless otherwise specified)

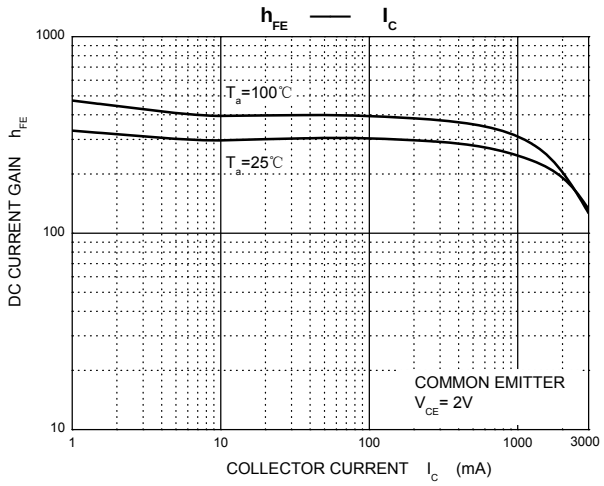
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C = 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C = 10mA, I_B=0	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}= 40 V, I_E=0			1	μA
Collector cut-off current	I_{CEO}	V_{CE}= 30 V, I_B=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 6 V, I_C=0			1	μA
DC current gain	h_{FE}	V_{CE}= 2 V, I_C= 1A	60		400	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C= 2A, I_B= 0.2 A			0.5	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C= 2A, I_B= 0.2 A			1.5	V
Transition frequency	f_T	V_{CE}= 5V, I_C=0.1A f =10MHz		90		MHz

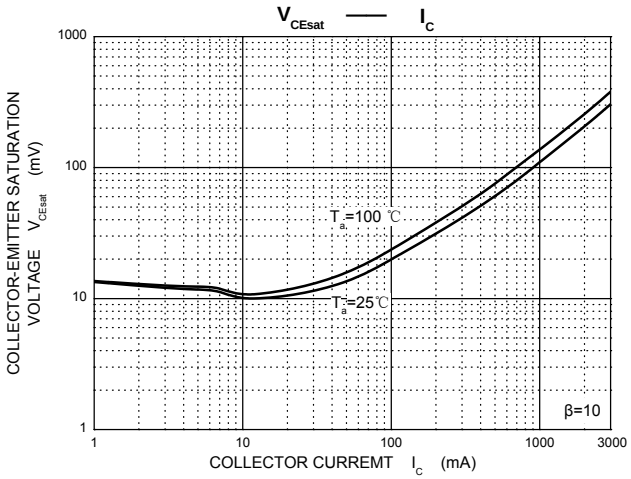
CLASSIFICATION OF h_{FE}

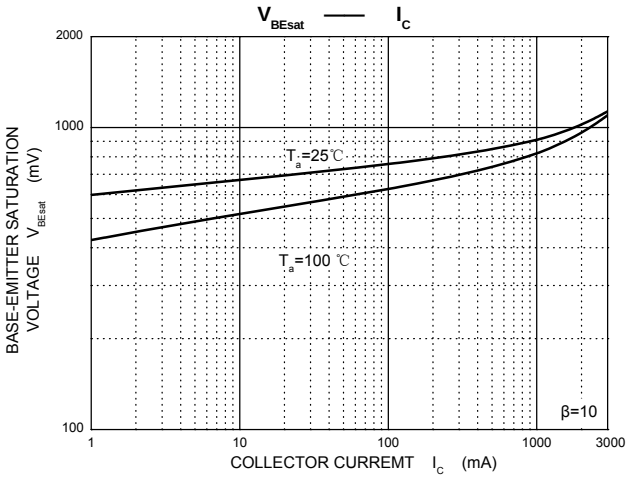
Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

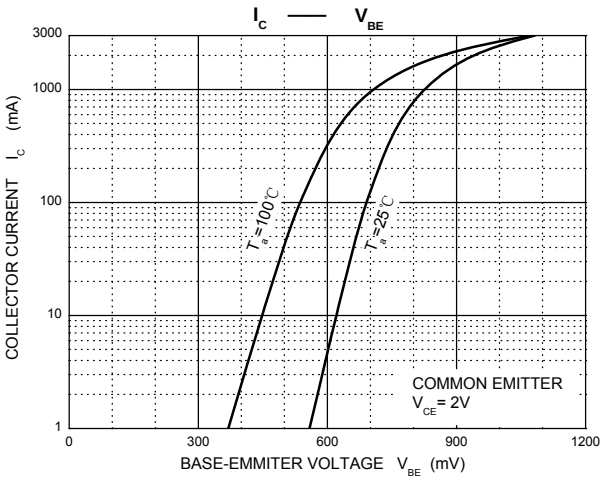
Typical Characteristics

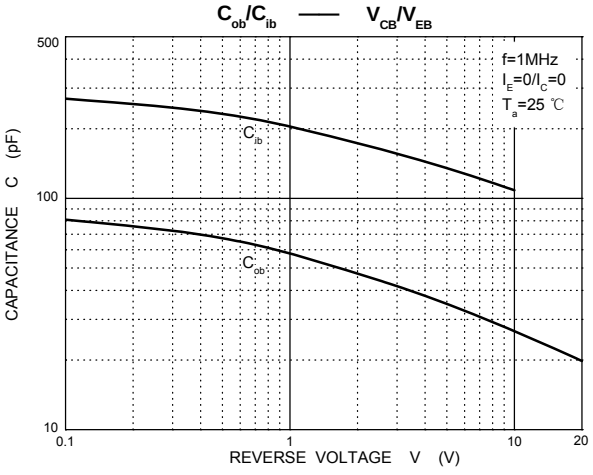


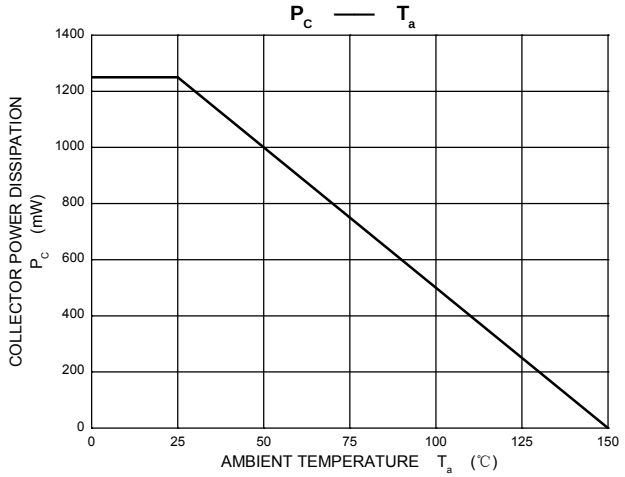




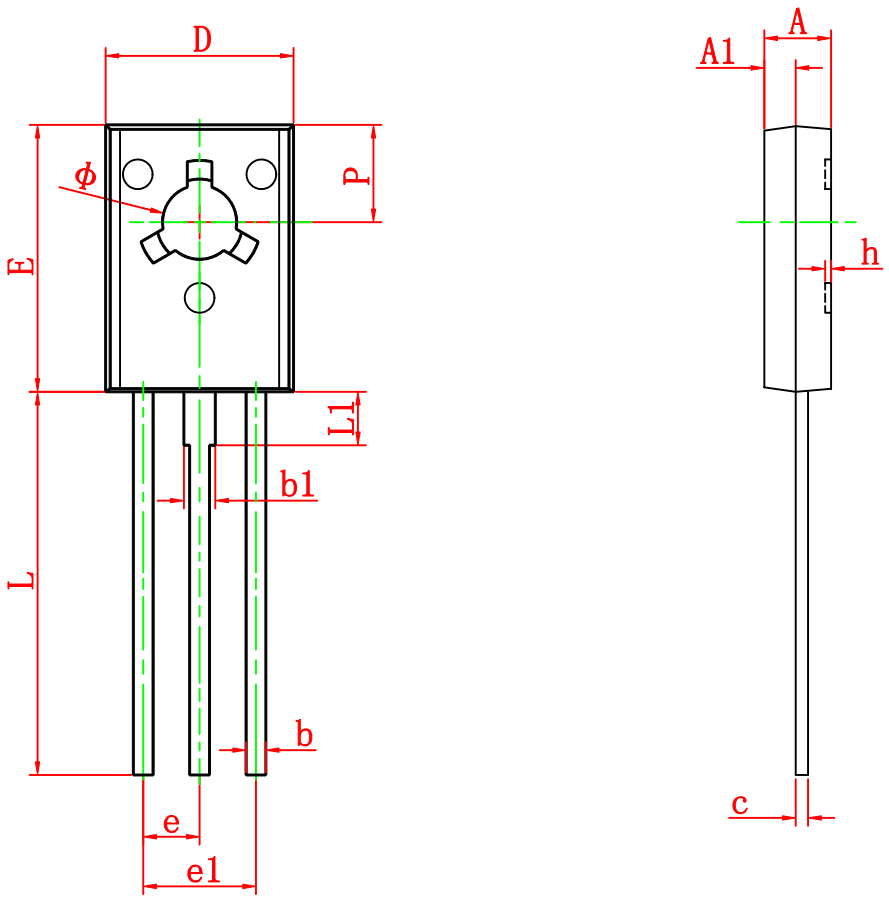








TO-126 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.500	2.900	0.098	0.114
A1	1.100	1.500	0.043	0.059
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.400	7.800	0.291	0.307
E	10.600	11.000	0.417	0.433
e	2.290 TYP		0.090 TYP	
e1	4.480	4.680	0.176	0.184
h	0.000	0.300	0.000	0.012
L	15.300	15.700	0.602	0.618
L1	2.100	2.300	0.083	0.091
P	3.900	4.100	0.154	0.161
Φ	3.000	3.200	0.118	0.126